

20V P-Channel MOSFET



SOP-8

Pin Definition:

8. Drain 1

7. Drain 1

6. Drain 2

5. Drain 2

1. Source 1 2. Gate 1 3. Source 2 4. Gate 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
	65 @ V _{GS} = -4.5V	-4.7
-20	100 @ V _{GS} = -2.5V	-3.8

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

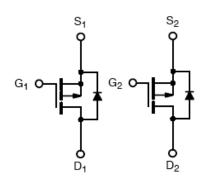
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing		
TSM9933DCS RL	SOP-8	2.5Kpcs / 13" Reel		

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	-4.7	Α	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	-20	Α	
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	-1.7	Α	
Maximum Power Dissipation	Ta = 25°C	- P _D	2	W	
	Ta = 70°C		1.3		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit	
Junction to Case Thermal Resistance	R⊖ _{JC}	30	°C/W	
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	80	°C/W	

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.



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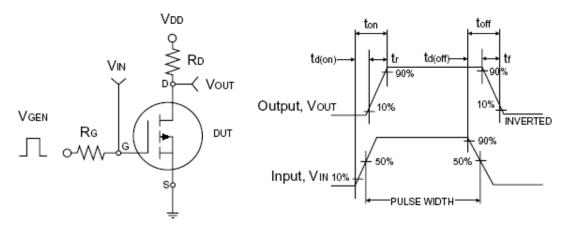


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		1		•		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.6		-1.4	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -20V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
On-State Drain Current ^a	$V_{DS} = -5V$, $V_{GS} = -4.5V$	I _{D(ON)}	-15			Α
Drain-Source On-State Resistance ^a	$V_{GS} = -4.5V$, $I_D = -4.7A$	Б	1	48	60	mΩ
	$V_{GS} = -2.5V$, $I_D = -3.8A$	$R_{DS(ON)}$		80	100	
Forward Transconductance ^a	$V_{DS} = -10V$, $I_{D} = -4.7A$	9 _{fs}		11		S
Diode Forward Voltage	$I_S = -1.7A$, $V_{GS} = 0V$	V_{SD}		-0.8	-1.2	V
Dynamic ^b						
Total Gate Charge		Q_g		6	9	
Gate-Source Charge	$V_{DS} = -10V, I_D = -4.7A,$ $V_{GS} = -4.5V$	Q_gs		1.4		nC
Gate-Drain Charge		Q_{gd}	-	1.9		
Input Capacitance	\\ - 40\\ \\ - 0\\	C _{iss}		640		
Output Capacitance	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		180		pF
Reverse Transfer Capacitance		C _{rss}		90		
Switching ^c						
Turn-On Delay Time	$V_{DD} = -10V, R_L = 10\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$ $R_G = 6\Omega$	t _{d(on)}		22	35	
Turn-On Rise Time		t _r		35	55	20
Turn-Off Delay Time		t _{d(off)}		45	70	nS
Turn-Off Fall Time		t _f		25	50	

Notes:

- a. pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

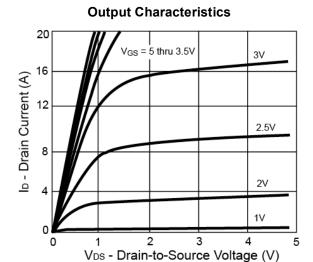




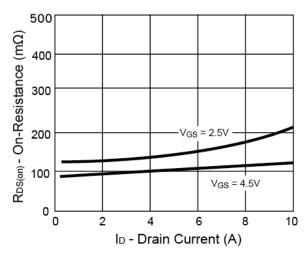
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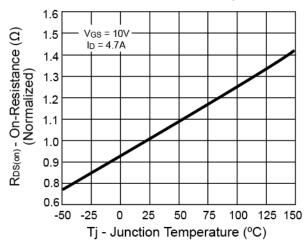
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



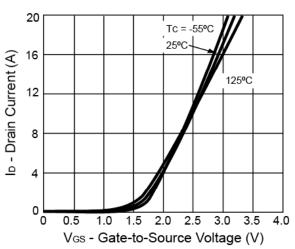
On-Resistance vs. Drain Current



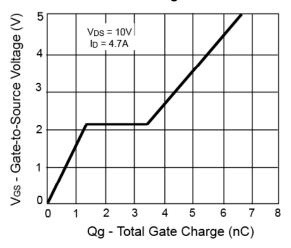
On-Resistance vs. Junction Temperature



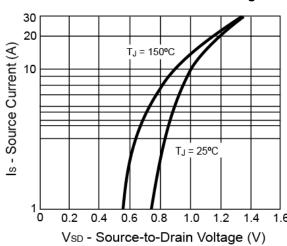
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



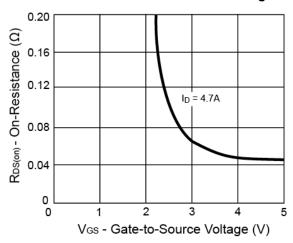


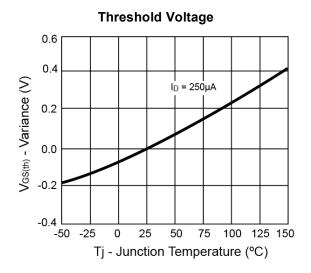
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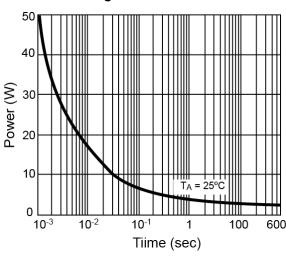
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

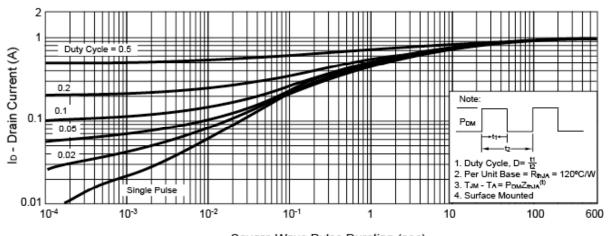




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)



INCHES

0.05BSC

MAX.

0.196

0.157

0.068

0.019

0.009

7°

0.244

0.019

0.049

MIN

0.189

0.150

0.054

0.014

0.016

0.004

0°

0.229

0.010



SOP-8 DIMENSION

MAX

5.00

4.00

1.75

0.49

1.25

0.25

7°

6.20

0.50

MILLIMETERS

1.27BSC

MIN

4.80

3.80

1.35

0.35

0.40

0.10

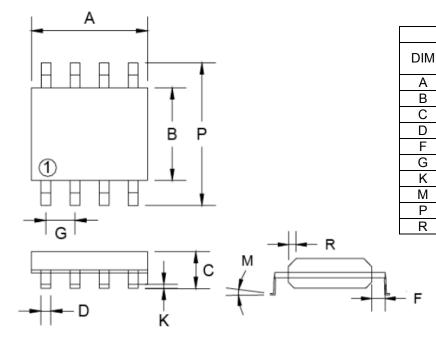
0°

5.80

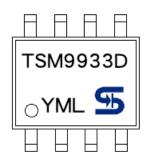
0.25



SOP-8 Mechanical Drawing



Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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